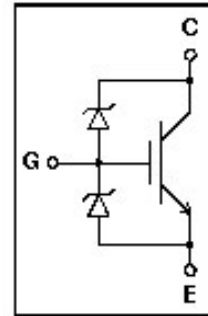


Delphi Ignition IG-2055

► Description

Insulated-gate Bipolar Transistors (IGBTs) from Delphi are cost-effective output drivers for automotive ignition systems. These devices are optimized for ruggedness and low saturation voltage. The on-board over-voltage clamp protects the device during open-secondary conditions and provides a breakdown voltage that is tightly controlled and nearly independent of temperature. These devices can be supplied as bare die or in TO-220 plastic packages.



► Features

- $BV_{ces} = 550 \text{ V}$
- $V_{ce \text{ sat}} = 1.8 \text{ V}$
- $I_c = 12 \text{ A}$
- Logic-level gate drive
- On-board over-voltage clamp
- ESD protection for gate electrode
- Reverse-battery protection
- Low saturation voltage
- High temperature capability (175°C)
- High energy capability (300mJ)

Absolute Maximum Ratings ($T_j=25^\circ\text{C}$)			
Symbol	Parameter	Ratings	Unit
V_{ge}	Gate-Emitter Voltage	± 12	V
V_{ce}	Collector-Emitter Voltage	580	V
I_{ce}	Collector Current (continuous)	18	A
E_{as}	Avalanche Energy	400	mJ
T_i	Operating Temp. (junction)	175	$^\circ\text{C}$

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Specifications											
Symbol	Parameter	25°C			-40°C			150°C			Units
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
BV _{ecs}	Collector-Emitter Breakdown Voltage I _C =10mA, R _{ge} =300ohms	630	660	680	630	660	680	630	660	680	V
BV _{ces}	Emitter-Collector Breakdown Voltage I _C =1mA	20			20			20			V
I _{ces}	Collector-Emitter Leakage Current V _{ce} =360V, V _{ge} =0V			20			10			200	μA
V _{ce(sat)}	Collector-Emitter Saturation Voltage V _{ge} =3.5V, I _c =12A		1.2	1.7		1.3	1.8		1.1	1.6	V
V _{ge(th)}	Gate Threshold V _{ge} =V _{ce} , I _c =1.0mA	1.2	1.4	2.1	1.2	1.5	2.3	0.7	0.9	1.9	V
BV _{geo}	Gate-Emitter Clamp Breakdown Voltage V _{ce} =Open, I _{ge} =5.0mA	17	19	22	17	19	22	17	19	22	V
I _{ge}	Gate-Emitter Bias Current V _{ge} =10V, V _{ce} =0V			5			5			10	μA
T _{d(off)}	Turn off Delay (90% V _G to 90% I _C) V _{cc} =20V, V _{ge} =5V, R _g =500			5			5			5	μsec
T _f	Fall Time (90% I _c to 10% I _c) V _{cc} =20V, V _{ge} =5V, R _g =500ohms			10			10			13	μs